Features

- Fast 5V Read Access Time 35 ns
- Command Table Architecture
 - Internal Program Control and Timer
- 12V Program and Erase
 - Fast Chip Erase Time 0.5 Second Maximum
 - Word-by-word Programming 20 μs/Word Typical
- Hardware Data Protection
- Low-power CMOS Operation
 - 100 µA Maximum Standby
 - 30 mA Maximum Active at 5 MHz
- JEDEC Standard Packages
 - 44-lead PLCC
 - 40-lead VSOP (10 mm x 14 mm)
- Pin-compatible with Atmel's AT27C1024 and AT49F1024/1025
- High-reliability CMOS Technology
 - 2000V ESD Protection
 - 200 mA Latchup Immunity
- CMOS and TTL Compatible Inputs and Outputs
- 100 Write Cycles Guaranteed

Description

The AT27RW1024 is a low-power, high-performance 1,048,576-bit electrically-rewriteable programmable read-only memory (RWPROM) organized 64K x 16 bits. It requires only one 5V power supply in normal read mode operation. Any word can be accessed in less than 35 ns, eliminating the need for speed reducing WAIT states.

(continued)

1-megabit

 $(64K \times 16)$

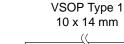
PROM

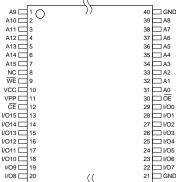
Rewriteable

AT27RW1024

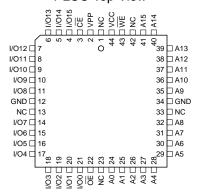
Pin Configurations

Pin Name	Function
A0 - A15	Addresses
CE	Chip Enable
ŌĒ	Output Enable
WE	Write Enable
I/O0 - I/O15	Data Inputs/Outputs
NC	No Connect





PLCC Top View



Rev. 1415A-06/99

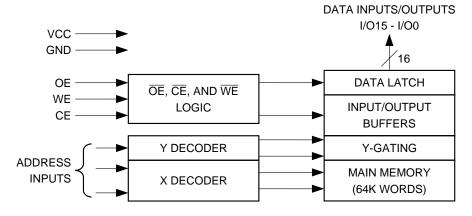




The x16 organization makes this part ideal for high-performance 16- and 32-bit DSP and microprocessor systems. The AT27RW1024 is pin-compatible with Atmel's AT49F1024/1025 and AT27C1024. In read mode, the AT27RW1024 typically consumes 15 mA. Standby mode supply current is typically less than 10 μ A. Reprogramming

the AT27RW1024 is performed by erasing the entire chip and then programming on a word-by-word basis. The program and erase functions are performed with $V_{CC} = 5V$ and $V_{PP} = 12V$. Programming time is 20 µs per word typical. 100 program and erase cycles are guaranteed.

Block Diagram



Device Operation

READ: When \overline{CE} and \overline{OE} are low and \overline{WE} is high, the data stored at the memory location determined by the address pins is asserted on the outputs. The outputs are put in the high impedance state whenever \overline{CE} or \overline{OE} is high. This dual-line control gives designers flexibility in preventing bus contention.

CHIP ERASE: The chip erase will erase all words to an FFFFH. The chip erase command is a six bus cycle operation. The address (5555H) is latched on the falling edge of the sixth cycle while the 10H data input is latched on the rising edge of WE. The chip erase starts after the rising edge of WE of the sixth cycle. Please see "Chip Erase Cycle Waveforms" on page 7. The chip erase operation is internally controlled; it will automatically time to completion. After a chip erase, the device will return to the read mode. Chip erase requires $V_{CC} = 5V$ and $V_{PP} = 12V$.

WORD PROGRAMMING: Once the memory array is erased, the device is programmed (to a logical "0") on a word-by-word basis. Please note that a data "0" cannot be programmed back to a "1"; only erase operations can convert "0"s to "1"s. Programming is accomplished via the internal device command register and is a 4 bus cycle operation (please refer to the Command Definitions table). The device will automatically generate the required internal program pulses.

The program cycle has addresses latched on the falling edge of WE or CE, whichever occurs last, and the data latched on the rising edge of WE or CE, whichever occurs first. Programming is completed after the specified t_{BP} cycle time. Programming requires $V_{PP} = 12V$ and $V_{CC} = 5V$.

PRODUCT IDENTIFICATION: The product identification mode identifies the device and manufacturer as Atmel. It may be accessed by hardware or software operation. The hardware operation mode can be used by an external programmer to identify the correct programming algorithm for the Atmel product.

For details, see Operating Modes (for hardware operation) or Software Product Identification. The manufacturer and device code is the same for both modes.

HARDWARE DATA PROTECTION: Hardware features protect against inadvertent programs to the AT27RW1024 in the following ways: (a) V_{CC} sense: if V_{CC} is below 3.8V (typical), the program function is inhibited. (b) <u>Program inhibit:</u> holding any one of \overline{OE} low, \overline{CE} high or \overline{WE} high inhibits program cycles. (c) Noise filter: Pulses of less than 15 ns (typical) on the \overline{WE} or \overline{CE} inputs will not initiate a program cycle.

Command Definition (in Hex)

Command	Bus	1st Cy		2nd Cyc			Bus cle	4th Cy	Bus cle	5th Cy		6th Cy	Bus cle
Sequence	Cycles	Addr	Data	Addr	Data	Addr	Data	Addr	Data	Addr	Data	Addr	Data
Read	1	Addr	D _{OUT}										
Chip Erase	6	5555	AA	2AAA	55	5555	80	5555	AA	2AAA	55	5555	10
Word Program	4	5555	AA	2AAA	55	5555	A0	Addr	D _{IN}				
Product ID Entry	3	5555	AA	2AAA	55	5555	90						
Product ID Exit	1	xxxx	F0										

Note: The DATA FORMAT in each bus cycle is as follows: I/O15 - I/O8 (Don't Care); I/O7 - I/O0 (Hex).

Absolute Maximum Ratings*

Temperature Unde	er Bias	55°C to +125°C
Storage Temperati	ure	65°C to +150°C
All Input Voltages (including NC Pins with Respect to Gr	s) round	0.6V to +6.25V
All Output Voltages with Respect to Gr	s round	0.6V to V _{CC} + 0.6V
Voltage on OE with Respect to Gr	round	0.6V to +13.5V

*NOTICE:

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.





DC and AC Operating Range

		AT27RW1024-35	AT27RW1024-45	AT27RW1024-55	AT27RW1024-70
Operating Temperature (Cose)	Com.	0°C - 70°C	0°C - 70°C	0°C - 70°C	0°C - 70°C
Operating Temperature (Case)	Ind.	-40°C - 85°C	-40°C - 85°C	-40°C - 85°C	-40°C - 85°C
V _{CC} Power Supply		5V ± 10%	5V ± 10%	5V ± 10%	5V ± 10%

Operating Modes

Mode	CE	OE	WE	V_{PP}	Ai	1/0
Read	V _{IL}	V _{IL}	V _{IH}	X ⁽¹⁾⁽⁷⁾	Ai	D _{OUT}
Program/Erase ⁽²⁾	V _{IL}	V _{IH}	V _{IL}	V _{PP}	Ai	D _{IN} /X
Standby	V _{IH}	X ⁽¹⁾	X ⁽¹⁾	X ⁽¹⁾⁽⁷⁾	X ⁽¹⁾	High Z
December /France labilit	V _{IL}	V_{IH}	V _{IL}	X ⁽¹⁾⁽⁷⁾	X ⁽¹⁾	
Program/Erase Inhibit	X ⁽¹⁾	X ⁽¹⁾	V _{IH}	V _{PP}	X ⁽¹⁾	
Program/Erase Verify	X ⁽¹⁾	V _{IL}	X ⁽¹⁾	V _{PP}	Ai	D _{OUT}
Output Disable	X ⁽¹⁾	V _{IH}	X ⁽¹⁾	X ⁽¹⁾⁽⁷⁾		High Z
Product Identification						
Handrian	V			X ⁽⁴⁾	A1 - A15 = V _{IL} , A9 = V _H , (3) A0 = V _{IL}	Manufacturer Code ⁽⁶⁾
Hardware	V _{IL}	V_{IL}	V _{IH}	X ⁽⁴⁾	A1 - A15 = V _{IL} , A9 = V _H , (3) A0 = V _{IH}	Device Code ⁽⁶⁾
C-#(5)				X ⁽⁴⁾	A0 = V _{IL} , A1 - A15 = V _{IL}	Manufacturer Code ⁽⁶⁾
Software ⁽⁵⁾				X ⁽⁴⁾	A0 = V _{IH} , A1 - A15 = V _{IL}	Device Code ⁽⁶⁾

- Notes: 1. X can be V_{IL} or V_{IH} .
 - 2. Refer to AC Programming and Erasing Waveforms.
 - 3. $V_H = 12.0V \pm 0.5V$.
 - 4. X can be V_{CC} or V_{PP}
 - 5. See details under Software Product Identification Entry/Exit.
 - 6. Manufacturer Code: 001EH, Device Code: 0051H.
 - 7. For customers building field-upgradable systems, X can be 12.0V.

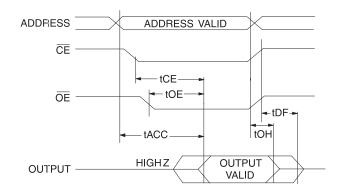
DC Characteristics

Symbol	Parameter	Condition	Min	Max	Units
ILI	Input Load Current	$V_{IN} = 0V \text{ to } V_{CC}$		10	μΑ
I _{LO}	Output Leakage Current	V _{I/O} = 0V to V _{CC}		10	μΑ
I _{SB1}	V _{CC} Standby Current CMOS	$\overline{\text{CE}} = \text{V}_{\text{CC}} - 0.3 \text{V to V}_{\text{CC}}$		100	μA
I _{SB2}	V _{CC} Standby Current TTL	$\overline{\text{CE}}$ = 2.0V to V _{CC}		1	mA
I _{CC}	V _{CC} Active Current	f = 5 MHz; I _{OUT} = 0 mA		30	mA
I _{PP}	Program or Erase Current	Word Program, Chip Erase in Progress		25	mA
V _{IL}	Input Low Voltage			0.8	V
V _{IH}	Input High Voltage		2.0		V
V _{OL}	Output Low Voltage	I _{OL} = 2.1 mA		0.45	V
V _{OH1}	Output High Voltage	I _{OH} = -400 μA	2.4		V

AC Read Characteristics

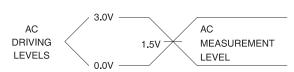
		AT27RW1024-35		AT27RW1024-45		AT27RW1024-55		AT27RW1024-70		
Symbol	Parameter	Min	Max	Min	Max	Min	Max	Min	Max	Units
t _{ACC}	Address to Output Delay		35		45		55		70	ns
t _{CE} ⁽¹⁾	CE to Output Delay		35		45		55		70	ns
t _{OE} ⁽²⁾	OE to Output Delay	0	15		18		25		25	ns
t _{DF} ⁽³⁾⁽⁴⁾	CE or OE to Output Float	0	15		18	0	25		25	ns
t _{OH}	Output Hold from OE, CE or Address, whichever occurred first	7		7		7		7		ns

AC Read Waveforms⁽¹⁾⁽²⁾⁽³⁾⁽⁴⁾



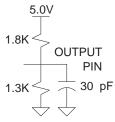
- Notes: 1. $\overline{\text{CE}}$ may be delayed up to t_{ACC} t_{CE} after the address transition without impact on t_{ACC} .
 - 2. $\overline{\text{OE}}$ may be delayed up to t_{CE} t_{OE} after the falling edge of $\overline{\text{CE}}$ without impact on t_{CE} or by t_{ACC} t_{OE} after an address change without impact on t_{ACC} .
 - 3. t_{DF} is specified from \overline{OE} or \overline{CE} whichever occurs first ($C_L = 5 \text{ pF}$).
 - 4. This parameter is characterized and is not 100% tested.

Input Test Waveforms and Measurement Level



 t_R , $t_F < 5 \text{ ns}$

Output Test Load



Pin Capacitance

 $f = 1 \text{ MHz}, T = 25^{\circ}C^{(1)}$

Symbol	Тур	Max	Units	Conditions
C _{IN}	4	6	pF	$V_{IN} = 0V$
C _{OUT}	8	12	pF	V _{OUT} = 0V

1. This parameter is characterized and is not 100% tested.



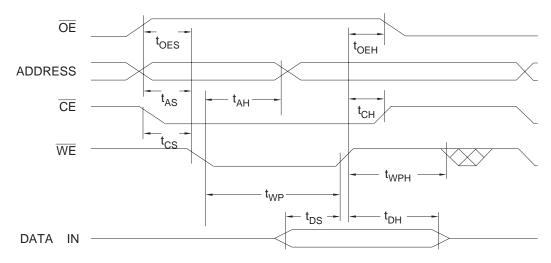


AC Word Load Characteristics

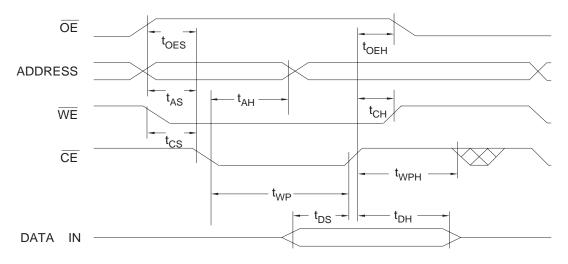
Symbol	Parameter	Min	Max	Units
t _{AS} , t _{OES}	Address, OE Set-up Time	0		ns
t _{AH}	Address Hold Time	50		ns
t _{CS}	Chip Select Set-up Time	0		ns
t _{CH}	Chip Select Hold Time	0		ns
t _{WP}	Write Pulse Width (WE or CE)	90		ns
t _{DS}	Data Set-up Time	50		ns
t _{DH} , t _{OEH}	Data, OE Hold Time	0		ns
t _{WPH}	Write Pulse Width High	90		ns

AC Word Load Waveforms

WE Controlled



CE Controlled

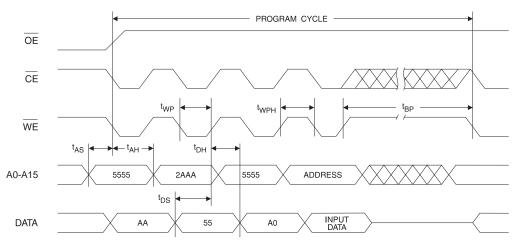


AT27RW1024

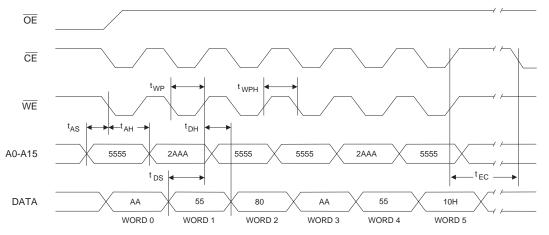
Program Cycle Characteristics

Symbol	Parameter	Min	Тур	Max	Units
t _{BP}	Word Programming Time		20	50	μs
t _{AS}	Address Set-up Time	0			ns
t _{AH}	Address Hold Time	50			ns
t _{DS}	Data Set-up Time	50			ns
t _{DH}	Data Hold Time	0			ns
t _{WP}	Write Pulse Width	90			ns
t _{WPH}	Write Pulse Width High	90			ns
t _{EC}	Erase Cycle Time			500	ms

Program Cycle Waveforms



Chip Erase Cycle Waveforms

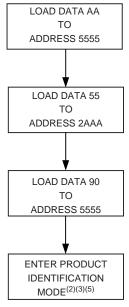


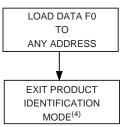
Notes: 1. \overline{OE} must be high only when \overline{WE} and \overline{CE} are both low.





Software Product Identification Entry⁽¹⁾ Software Product Identification Exit⁽¹⁾





Notes: 1. Data Format: I/O15 - I/O8 (Don't Care); I/O7 - I/O0 (Hex);

Address Format: A14 - A0 (Hex).

2. A1 - A15 = V_{IL} .

Manufacture Code is read for $A0 = V_{IL}$; Device Code is read for $A0 = V_{IH}$.

- 3. The device does not remain in identification mode if powered down.
- 4. The device returns to standard operation mode.
- 5. Manufacturer Code: 001EH Device Code: 0051H

Ordering Information

tacc	t _{ACC} I _{CC} (mA) (ns) Active Standby				
			Ordering Code	Package	Operation Range
35	30	0.1	AT27RW1024-35JC	44J	Commercial
			AT27RW1024-35VC	40V	(0° to 70°C)
	30	0.1	AT27RW1024-35JI	44J	Industrial
			AT27RW1024-35VI	40V	(-40° to 85°C)
45	30	0.1	AT27RW1024-45JC	44J	Commercial
			AT27RW1024-45VC	40V	(0° to 70°C)
	30	0.1	AT27RW1024-45JI	44J	Industrial
			AT27RW1024-45VI	40V	(-40° to 85°C)
55	30	0.1	AT27RW1024-55JC	44J	Commercial
			AT27RW1024-55VC	40V	(0° to 70°C)
	30	0.1	AT27RW1024-55JI	44J	Industrial
			AT27RW1024-55VI	40V	(-40° to 85°C)
70	30	0.1	AT27RW1024-70JC	44J	Commercial
			AT27RW1024-70VC	40V	(0° to 70°C)
	30	0.1	AT27RW1024-70JI	44J	Industrial
			AT27RW1024-70VI	40V	(-40° to 85°C)

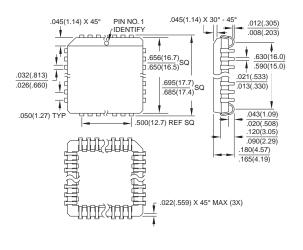
	Package Type
44J	44-lead, Plastic J-leaded Chip Carrier (PLCC)
40V	40-lead, Thin Small Outline Package (VSOP) (10 mm x 14 mm)





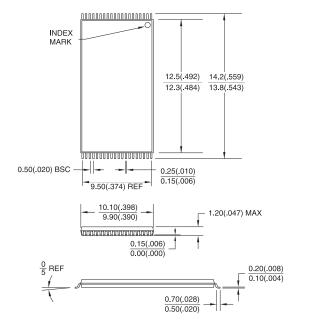
Packaging Information

44J, 44-lead, Plastic J-leaded Chip Carrier (PLCC) Dimensions in Inches and (Millimeters)*
JEDEC STANDARD MS-018 AC



*Controlling dimension: millimeters

40V, 40-lead, Plastic Thin Small Outline Package (VSOP) Dimensions in Millimeters and (Inches)*



*Controlling dimension: millimeters



Atmel Headquarters

Corporate Headquarters 2325 Orchard Parkway San Jose, CA 95131 TEL (408) 441-0311 FAX (408) 487-2600

Europe

Atmel U.K., Ltd. Coliseum Business Centre Riverside Way Camberley, Surrey GU15 3YL England TEL (44) 1276-686-677 FAX (44) 1276-686-697

Asia

Atmel Asia, Ltd.
Room 1219
Chinachem Golden Plaza
77 Mody Road Tsimhatsui
East Kowloon
Hong Kong
TEL (852) 2721-9778
FAX (852) 2722-1369

Japan

Átmel Japan K.K. 9F, Tonetsu Shinkawa Bldg. 1-24-8 Shinkawa Chuo-ku, Tokyo 104-0033 Japan TEL (81) 3-3523-3551 FAX (81) 3-3523-7581

Atmel Operations

Atmel Colorado Springs 1150 E. Cheyenne Mtn. Blvd. Colorado Springs, CO 80906 TEL (719) 576-3300 FAX (719) 540-1759

Atmel Rousset

Zone Industrielle 13106 Rousset Cedex France TEL (33) 4-4253-6000 FAX (33) 4-4253-6001

> Fax-on-Demand North America: 1-(800) 292-8635 International: 1-(408) 441-0732

e-mail literature@atmel.com

Web Site http://www.atmel.com

BBS 1-(408) 436-4309

© Atmel Corporation 1999.

Atmel Corporation makes no warranty for the use of its products, other than those expressly contained in the Company's standard warranty which is detailed in Atmel's Terms and Conditions located on the Company's web site. The Company assumes no responsibility for any errors which may appear in this document, reserves the right to change devices or specifications detailed herein at any time without notice, and does not make any commitment to update the information contained herein. No licenses to patents or other intellectual property of Atmel are granted by the Company in connection with the sale of Atmel products, expressly or by implication. Atmel's products are not authorized for use as critical components in life support devices or systems.

Marks bearing $^{\text{\tiny{8}}}$ and/or $^{\text{\tiny{TM}}}$ are registered trademarks and trademarks of Atmel Corporation.

Terms and product names in this document may be trademarks of others.

